

SEMiX[®] 1s

Rectifier Diode Module SEMiX191KD16s

Features

- Terminal height 17 mm
- Chips soldered directly to isolated substrate

Typical Applications*

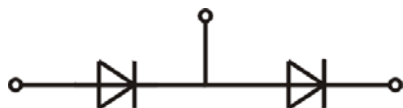
- Input Bridge Rectifier for AC/DC motor control
- Power supply

Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
Rectifier Diode				
I _{FAV}	sin. 180°	T _c = 85 °C	190	A
		T _c = 100 °C	145	A
I _{FSM}	10 ms	T _j = 25 °C	6000	A
		T _j = 130 °C	5000	A
i ² t	10 ms	T _j = 25 °C	180000	A ² s
		T _j = 130 °C	125000	A ² s
V _{RSM}		1700	V	
V _{RRM}		1600	V	
T _j		-40 ... 130	°C	
Module				
T _{stg}		-40 ... 125	°C	
V _{isol}	AC sinus 50Hz	1 min	4000	V
		1 s	4800	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Diode					
V _F	T _j = 25 °C, I _F = 500 A			1.5	V
V _(TO)	T _j = 130 °C			0.85	V
r _T	T _j = 130 °C			0.95	mΩ
I _{RD}	T _j = 130 °C, V _{RD} = V _{RRM}			12	mA
R _{th(j-c)}		per diode			K/W
					K/W
R _{th(j-c)}	sin. 180	per diode		0.18	K/W
					K/W
Module					
R _{th(c-s)}	per chip				K/W
	per module		0.075		K/W
M _s	to heat sink (M5)		3	5	Nm
M _t	to terminals (M6)		2.5	5	Nm
a				5 * 9,81	m/s ²
w			145		g



KD

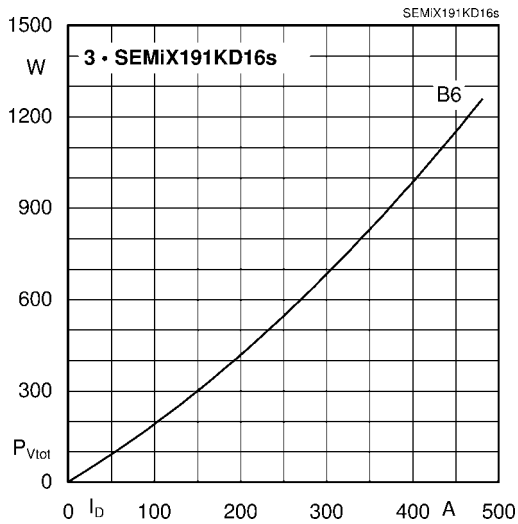


Fig. 4L: Power dissipation of three modules vs. direct current

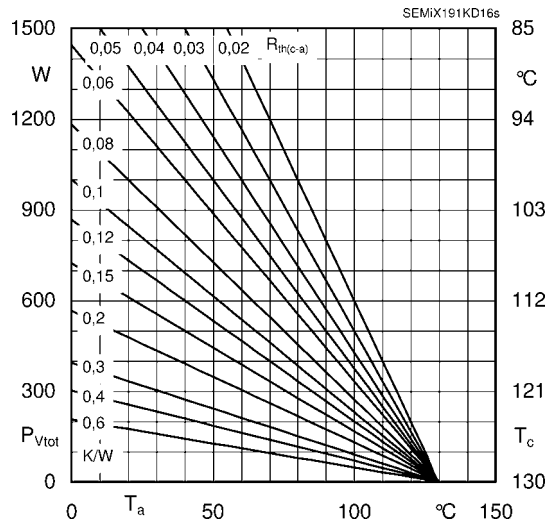


Fig. 4R: Power dissipation of three modules vs. case temperature

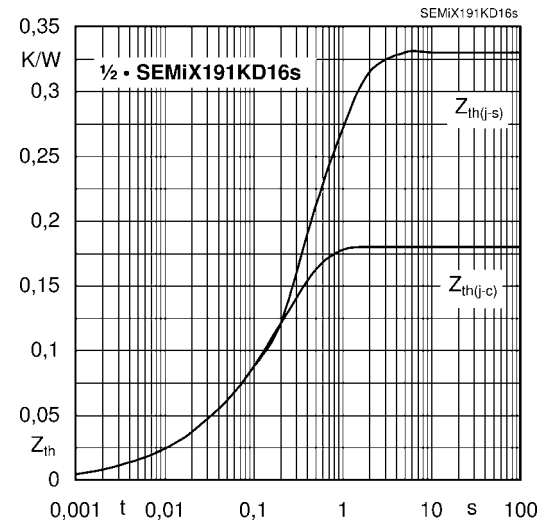


Fig. 6: Transient thermal impedance vs. time

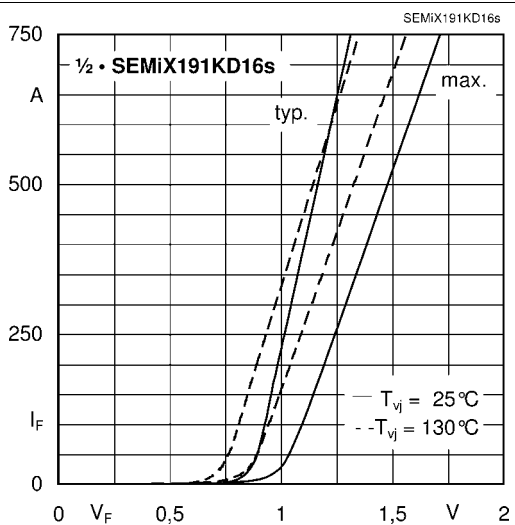


Fig. 7: On-state characteristics

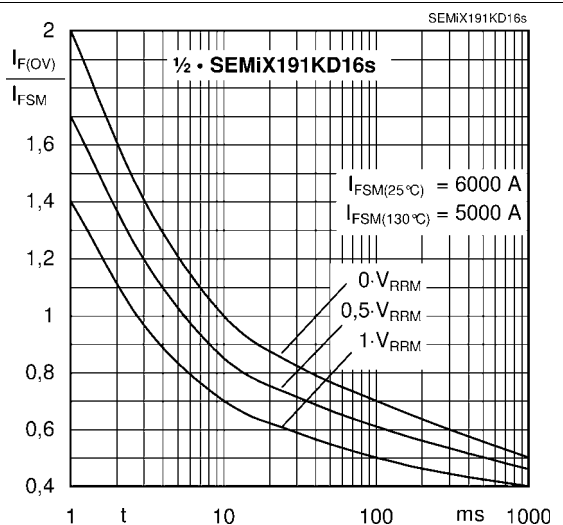


Fig. 8: Surge overload current vs. time

